Low-power dual buffer/line driver; 3-state

Rev. 9 — 11 February 2013

Product data sheet

1. General description

The 74AUP2G126 provides the dual non-inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input (nOE). A LOW level at pin nOE causes the output to assume a high-impedance OFF-state. This device has the input-disable feature, which allows floating input signals. The inputs are disabled when the output enable input nOE is LOW.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V. This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - ◆ JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - ◆ HBM JESD22-A114F Class 3A exceeds 5000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- Input-disable feature allows floating input conditions
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from −40 °C to +85 °C and −40 °C to +125 °C



3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AUP2G126DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74AUP2G126GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 \times 1.95 \times 0.5 mm	SOT833-1
74AUP2G126GF	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1 \times 0.5$ mm	SOT1089
74AUP2G126GD	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 3 \times 2 \times 0.5 mm	SOT996-2
74AUP2G126GM	–40 °C to +125 °C	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.6 \times 1.6 \times 0.5 mm	SOT902-2
74AUP2G126GN	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.2 \times 1.0 \times 0.35 mm	SOT1116
74AUP2G126GS	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1.0 \times 0.35$ mm	SOT1203

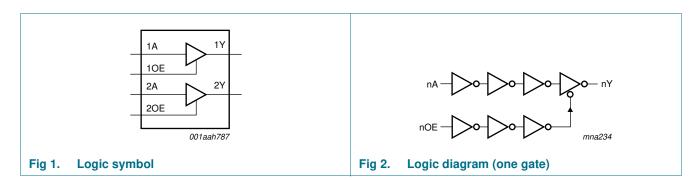
4. Marking

Table 2. Marking codes

142.0 2	
Type number	Marking code ^[1]
74AUP2G126DC	p26
74AUP2G126GT	p26
74AUP2G126GF	pN
74AUP2G126GD	p26
74AUP2G126GM	p26
74AUP2G126GN	pN
74AUP2G126GS	pN

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

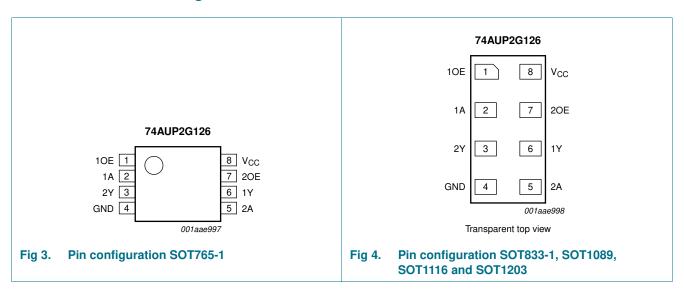
5. Functional diagram

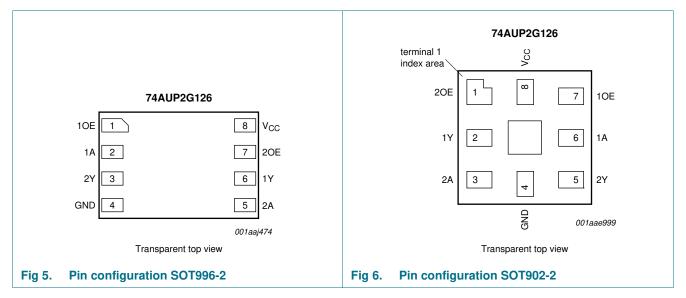


74AUP2G126

Pinning information

6.1 Pinning





6.2 Pin description

Table 3. Pin description

Symbol	Pin	Pin			
	SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-2			
10E, 20E	1, 7	7, 1	output enable input (active HIGH)		
1A, 2A	2, 5	6, 3	data input		
1Y, 2Y	6, 3	2, 5	data output		
GND	4	4	ground (0 V)		
V _{CC}	8	8	supply voltage		

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7. Functional description

Table 4. Function table[1]

Input nOE		Output
nOE	nA	nY
Н	L	L
Н	Н	Н
L	X	Z

^[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
V_{I}	input voltage		<u>[1]</u> –0.5	+4.6	V
I_{OK}	output clamping current	$V_O < 0 V$	-50	-	mA
V_{O}	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
I _O	output current	$V_O = 0 V \text{ to } V_{CC}$	-	±20	mA
I _{CC}	supply current		-	50	mA
I_{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	<u>[2]</u> -	250	mW

^[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		0.8	3.6	V
V _I	input voltage		0	3.6	V
V_O	output voltage	Active mode	0	V_{CC}	V
		Power-down mode; V _{CC} = 0 V	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	0	200	ns/V

^[2] For VSSOP8 packages: above 110 °C the value of P_{tot} derates linearly with 8.0 mW/K.
For XSON8 and XQFN8 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	5 °C					
V_{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.70 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 \text{ V}$	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$	-	-	$0.35 \times V_{CC}$	٧
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	٧
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	٧
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_{O} = -20 \mu A$; $V_{CC} = 0.8 \text{ V}$ to 3.6 V	V _{CC} - 0.1	-	-	V
		$I_O = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75 \times V_{CC}$	-	-	٧
		$I_O = -1.7 \text{ mA}$; $V_{CC} = 1.4 \text{ V}$	1.11	-	-	٧
		$I_O = -1.9 \text{ mA}$; $V_{CC} = 1.65 \text{ V}$	1.32	-	-	٧
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_O = -3.1 \text{ mA}$; $V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_O = -2.7 \text{ mA}$; $V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_O = -4.0 \text{ mA}$; $V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
l ₁	input leakage current	$V_{I} = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.1	μΑ
l _{OZ}	OFF-state output current	$V_{I} = V_{IH}$ or V_{IL} ; $V_{O} = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μΑ
I _{OFF}	power-off leakage current	V_{I} or $V_{O} = 0 \text{ V}$ to 3.6 V; $V_{CC} = 0 \text{ V}$	-	-	±0.2	μΑ
ΔI_{OFF}	additional power-off leakage current	$V_1 \text{ or } V_O = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.2	μΑ
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	0.5	μА

 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	ı	Min	Тур	Max	Unit
Δl _{CC}	additional supply current	data input; $V_I = V_{CC} - 0.6 \ V; I_O = 0 \ A;$ $V_{CC} = 3.3 \ V$	[1] -	-	-	40	μΑ
		nOE input; $V_I = V_{CC} - 0.6 \text{ V}$; $I_O = 0 \text{ A}$; $V_{CC} = 3.3 \text{ V}$	<u>[1]</u> -	-	-	110	μΑ
		all inputs; V_I = GND to 3.6 V; nOE = GND; V_{CC} = 0.8 V to 3.6 V	[2] -	-	-	1	μΑ
Cı	input capacitance	$V_I = GND \text{ or } V_{CC}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	0.9	-	pF
Co	output capacitance	output enabled; $V_O = GND$; $V_{CC} = 0 V$	-	-	1.7	-	рF
		output disabled; V_O = GND or V_{CC} ; V_{CC} = 0 V to 3.6 V	•	-	1.5	-	pF
T _{amb} = -	40 °C to +85 °C						
V _{IH}	HIGH-level input voltage	$V_{CC} = 0.8 \text{ V}$	($0.70 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V	($0.65 \times V_{CC}$	-	-	V
		V _{CC} = 2.3 V to 2.7 V	-	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	-	$0.30 \times V_{CC}$	V
		V _{CC} = 0.9 V to 1.95 V	-	-	-	$0.35 \times V_{CC}$	V
		V _{CC} = 2.3 V to 2.7 V	-	-	-	0.7	٧
		V _{CC} = 3.0 V to 3.6 V	-	-	-	0.9	٧
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}					
		$I_{O} = -20 \mu A$; $V_{CC} = 0.8 \text{ V}$ to 3.6 V	١	V _{CC} – 0.1	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	($0.7 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$		1.30	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$		1.97	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$		1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2	2.67	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2	2.55	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}					
		$I_O = 20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	_	-	-	0.1	V
		$I_O = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	-	$0.3 \times V_{\text{CC}}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	_	•	-	0.37	V
		$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	_	-	-	0.35	V
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	_	•	-	0.33	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	_	•	-	0.45	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	-	0.33	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	-	0.45	٧
l _I	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	_	-	-	±0.5	μΑ
l _{oz}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	-	±0.5	μΑ
OFF	power-off leakage current	V_{I} or $V_{O} = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	-	±0.5	μΑ

 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ΔI_{OFF}	additional power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V to 0.2 V		-	-	±0.6	μΑ
СС	supply current	V_I = GND or V_{CC} ; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V		-	-	0.9	μА
Δl _{CC}	additional supply current	data input; $V_I = V_{CC} - 0.6 \text{ V}$; $I_O = 0 \text{ A}$; $V_{CC} = 3.3 \text{ V}$	[1]	-	-	50	μΑ
		nOE input; $V_I = V_{CC} - 0.6 \text{ V}$; $I_O = 0 \text{ A}$; $V_{CC} = 3.3 \text{ V}$	[1]	-	-	120	μΑ
		all inputs; V_I = GND to 3.6 V; nOE = GND; V_{CC} = 0.8 V to 3.6 V	[2]	-	-	1	μА
Γ _{amb} = -	40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V		$0.75 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V		$0.70 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V		1.6	-	±0.6 μ 0.9 μ 50 μ 120 μ 1 μ 1 ν - ν - ν - ν 0.25 × V _{CC} ν 0.30 × V _{CC} ν 0.7 ν 0.9 ν - ν - ν - ν - ν - ν - ν - ν	V
		V_{CC} = 3.0 V to 3.6 V		2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V		-	-	$0.25 \times V_{CC}$	V
		V _{CC} = 0.9 V to 1.95 V		-	-	$0.30 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V		-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V		-	-	0.9	V
√ _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}					
		$I_O = -20 \mu A$; $V_{CC} = 0.8 \text{ V}$ to 3.6 V		$V_{CC}-0.11$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$		$0.6 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$		0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$		1.17	-	-	٧
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$		1.77	-	-	٧
		$I_O = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$		1.67	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$		2.40	-	-	V
		$I_O = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$		2.30	-	-	V
V OL	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}					
		I_O = 20 μ A; V_{CC} = 0.8 V to 3.6 V		-	-	0.11	V
		$I_O = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$		-	-	$0.33 \times V_{CC}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$		-	-	0.41	V
		$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$		-	-	0.39	V
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$		-	-	0.36	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$		-	-	0.50	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$		-	-	0.36	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$		-	-	0.50	V
I	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V		-	-	±0.75	μΑ
l _{oz}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V		-	-	±0.75	μА
OFF	power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V		-	-	±0.75	μА

 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μΑ
I _{CC}	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μΑ
ΔI_{CC}	additional supply current	data input; $V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	[1] -	-	75	μΑ
		nOE input; $V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	[1] -	-	180	μΑ
		all inputs; $V_I = GND$ to 3.6 V; nOE = GND; $V_{CC} = 0.8$ V to 3.6 V	[2] _	-	1	μΑ

^[1] One input at V_{CC} – 0.6 V, other input at V_{CC} or GND.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions		25 °C		-4	0 °C to +1	125 °C	Unit
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 pl				•		,	•		'
t _{pd}	propagation delay	nA to nY; see Figure 7							
		$V_{CC} = 0.8 \text{ V}$	-	20.6	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.8	5.5	10.5	2.5	11.7	12.9	ns
		V _{CC} = 1.4 V to 1.6 V	2.2	3.9	6.1	2.0	7.3	8.1	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	1.9	3.2	4.1	1.7	6.1	6.7	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	2.6	3.6	1.4	4.3	4.9	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.4	2.4	3.1	1.2	3.9	4.4	ns
t _{en}	enable time	nOE to nY; see Figure 8							
		$V_{CC} = 0.8 \text{ V}$	-	71.6	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.8	6.2	12.4	2.6	13.6	13.6	ns
		V _{CC} = 1.4 V to 1.6 V	2.3	4.2	6.9	2.2	7.4	7.7	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	1.9	3.3	5.3	1.7	5.9	6.2	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.5	2.4	3.6	1.4	3.8	4.1	ns
		V _{CC} = 3.0 V to 3.6 V	1.3	2.0	2.9	1.2	3.2	3.4	ns
t _{dis}	disable time	nOE to nY; see Figure 8 [4]							
		$V_{CC} = 0.8 \text{ V}$	-	10.3	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	2.6	4.2	6.2	2.9	6.4	6.5	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	2.1	3.2	4.4	2.2	4.6	4.7	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	2.1	3.1	4.4	1.7	4.6	4.8	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7	2.4	3.2	1.4	3.4	3.6	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.1	2.8	3.6	1.2	3.7	3.8	ns

^[2] To show I_{CC} remains very low when the input-disable feature is enabled.

 Table 8.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see <u>Figure 9</u>.

Symbol	Parameter	Conditions			25 °C		-40 °C to +125 °C			Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 10	pF						•	•		
t _{pd}	propagation delay	nA to nY; see Figure 7	[2]							
		$V_{CC} = 0.8 \text{ V}$		-	24.0	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.2	6.4	12.3	3.0	13.8	15.2	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.1	4.5	7.3	1.9	8.5	9.4	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.9	3.8	5.5	1.7	6.8	7.6	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		2.1	3.2	4.2	1.6	5.3	5.9	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.8	3.0	3.8	1.6	4.6	5.2	ns
t _{en}	enable time	nOE to nY; see Figure 8	[3]							
		$V_{CC} = 0.8 \text{ V}$		-	75.3	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.2	7.1	14.1	3.0	15.4	15.4	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.2	4.8	8.0	2.1	8.3	8.6	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.8	3.9	5.9	1.7	6.5	6.8	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.5	2.9	4.2	1.4	4.5	4.8	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.4	2.6	3.6	1.3	3.8	4.0	ns
t _{dis}	disable time	nOE to nY; see Figure 8	<u>[4]</u>							
		$V_{CC} = 0.8 \text{ V}$		-	12.2	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.5	5.3	7.6	3.3	7.9	7.9	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.2	4.1	5.6	2.1	5.7	5.9	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.4	4.2	5.7	1.7	5.8	6.0	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.9	3.2	4.1	1.4	4.3	4.5	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.4	4.1	5.0	1.3	5.2	5.3	ns
C _L = 15	pF									
t _{pd}	propagation delay	nA to nY; see Figure 7	[2]							
		$V_{CC} = 0.8 \text{ V}$		-	27.4	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.6	7.2	14.1	3.3	15.8	17.5	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		3.0	5.1	8.1	2.5	9.8	10.9	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.2	4.3	6.3	2.0	7.9	8.8	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		2.0	3.7	4.9	1.8	6.0	6.7	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.0	3.5	4.4	1.8	5.4	6.1	ns
t _{en}	enable time	nOE to nY; see Figure 8	[3]							
		$V_{CC} = 0.8 \text{ V}$		-	79.2	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.6	7.8	15.8	3.3	17.1	17.1	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		3.0	5.4	8.8	2.9	9.4	9.7	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.1	4.3	6.7	2.0	7.3	7.7	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.8	3.4	4.8	1.7	5.2	5.6	ns
	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.6	3.1	4.1	1.5	4.5	4.7	ns	

 Table 8.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions		25 °C		_4	10 °C to +1	25 °C	Unit
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
t _{dis}	disable time	nOE to nY; see Figure 8 [4]	'						
		$V_{CC} = 0.8 \text{ V}$	-	14.9	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	4.3	6.4	8.5	3.7	9.3	9.4	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	3.0	5.0	6.6	2.5	6.9	7.0	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	3.1	5.4	6.6	2.0	7.4	7.5	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	2.4	4.0	5.0	1.7	5.1	5.5	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	3.2	5.3	6.2	1.5	6.7	6.9	ns
C _L = 30 p	o F								
t _{pd}	propagation delay	nA to nY; see Figure 7							
		V _{CC} = 0.8 V	-	37.4	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	4.8	9.5	18.7	4.4	21.4	24.0	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	4.0	6.7	10.8	3.0	13.0	14.5	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	2.9	5.6	8.4	2.6	10.3	11.5	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	2.7	4.8	6.3	2.5	7.8	8.7	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.7	4.6	5.8	2.5	7.0	8.3	ns
t _{en}	enable time	nOE to nY; see Figure 8							
		V _{CC} = 0.8 V	-	90.6	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	4.7	10.0	20.4	4.3	22.0	22.0	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	3.0	6.9	11.3	3.7	12.0	12.5	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	2.6	5.6	8.6	3.2	9.5	10.1	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	2.3	4.5	6.3	2.9	6.8	7.3	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.2	4.2	5.8	2.7	6.4	6.7	ns
t _{dis}	disable time	nOE to nY; see Figure 8 [4]							
		$V_{CC} = 0.8 \text{ V}$	-	51.6	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	6.0	9.8	13.6	4.7	14.3	14.4	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	4.5	7.7	10.5	3.0	10.7	11.0	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	5.2	8.8	11.4	2.6	11.5	11.6	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	3.9	6.4	7.4	2.3	9.0	10.2	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	5.5	9.0	10.7	2.2	10.8	12.0	ns

 Table 8.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter Conditions				25 °C		-4	Unit		
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
$C_L = 5 pl$	F, 10 pF, 15 pF and	30 pF								
		output enabled; $f_i = 1 \text{ MHz}$; $V_I = \text{GND to } V_{\text{CC}}$	[5]							
		$V_{CC} = 0.8 \text{ V}$		-	2.7	-	-	-	-	pF
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		-	2.8	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		-	2.9	-	-	-	-	pF
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		-	3.0	-	-	-	-	pF
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-	3.6	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		-	4.2	-	-	-	-	pF

- [1] All typical values are measured at nominal V_{CC} .
- [2] t_{pd} is the same as t_{PLH} and t_{PHL} .
- [3] t_{en} is the same as t_{PZH} and t_{PZL} .
- [4] t_{dis} is the same as t_{PHZ} and t_{PLZ} .
- [5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o) \text{ where:}$

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

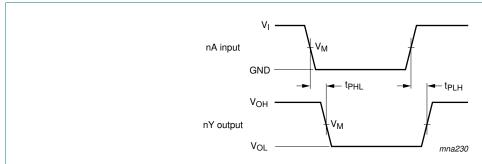
C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma (C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms



Measurement points are given in Table 9.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

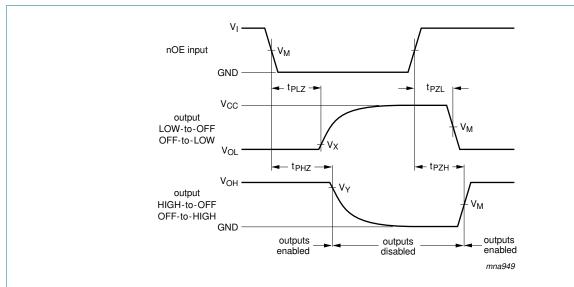
Fig 7. The data input (nA) to output (nY) propagation delays

Table 9. Measurement points

Supply voltage	Output	Input		
V _{CC}	V _M	V _M	VI	$t_r = t_f$
0.8 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{CC}	≤ 3.0 ns

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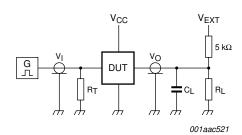
Measurement points are given in <u>Table 10</u>.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 8. Enable and disable times

Table 10. Measurement points

Supply voltage	Input	Output	Output					
V _{CC}	V _M	V _M	V _X	V _Y				
0.8 V to 1.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{OL} + 0.1 V$	$V_{OH}-0.1\ V$				
1.65 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{OL} + 0.15 V$	V _{OH} – 0.15 V				
3.0 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{OL} + 0.3 V$	$V_{OH}-0.3\ V$				



Test data is given in Table 11.

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 9. Test circuit for measuring switching times

Table 11. Test data

Supply voltage	Load	V _{EXT}			
V _{CC}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	$5~\text{k}\Omega$ or 1 $\text{M}\Omega$	open	GND	$2\times V_{CC}$

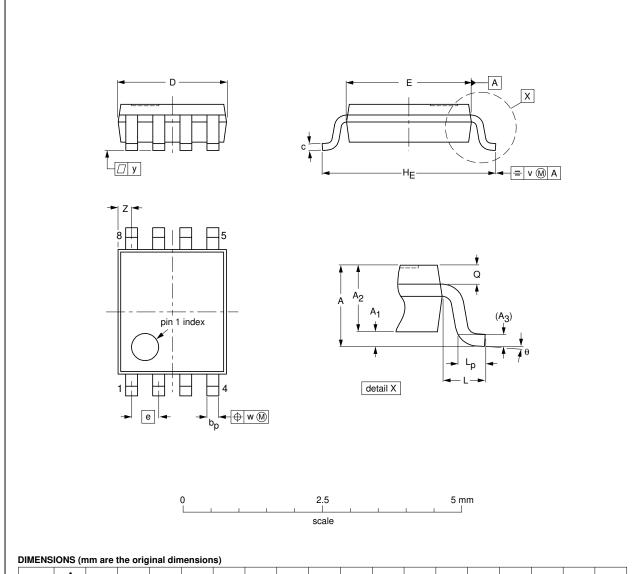
[1] For measuring enable and disable times R_L = 5 k Ω .

For measuring propagation delays, set-up and hold times and pulse width R_L = 1 $M\Omega$.

13. Package outline

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



UNIT	A max.	A ₁	A ₂	А3	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT765-1		MO-187			02-06-07

Fig 10. Package outline SOT765-1 (VSSOP8)

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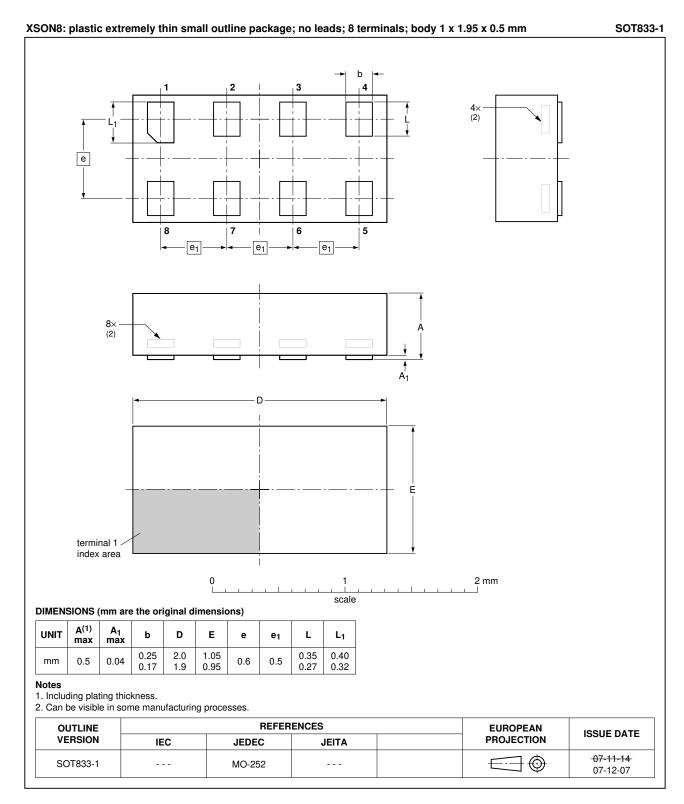


Fig 11. Package outline SOT833-1 (XSON8)

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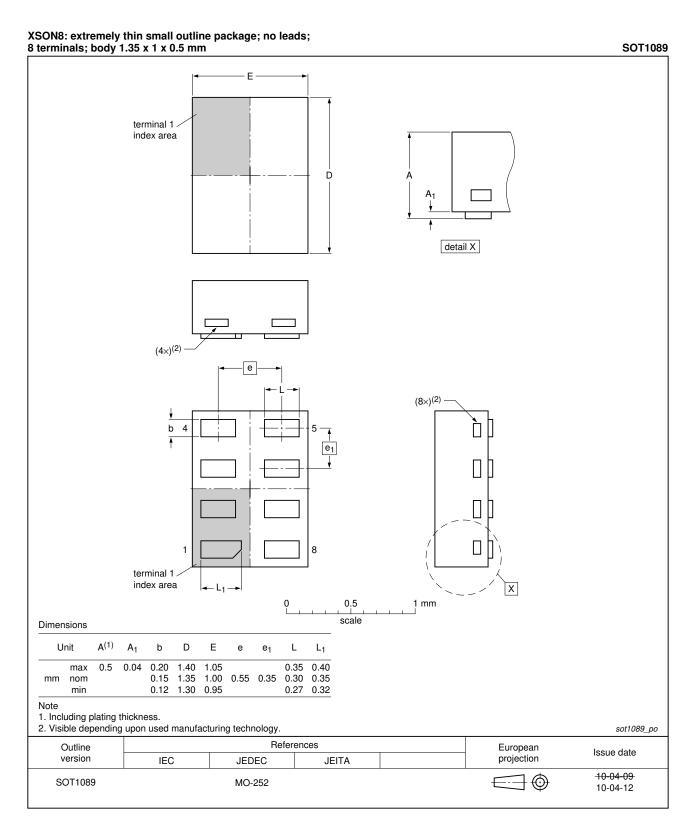


Fig 12. Package outline SOT1089 (XSON8)

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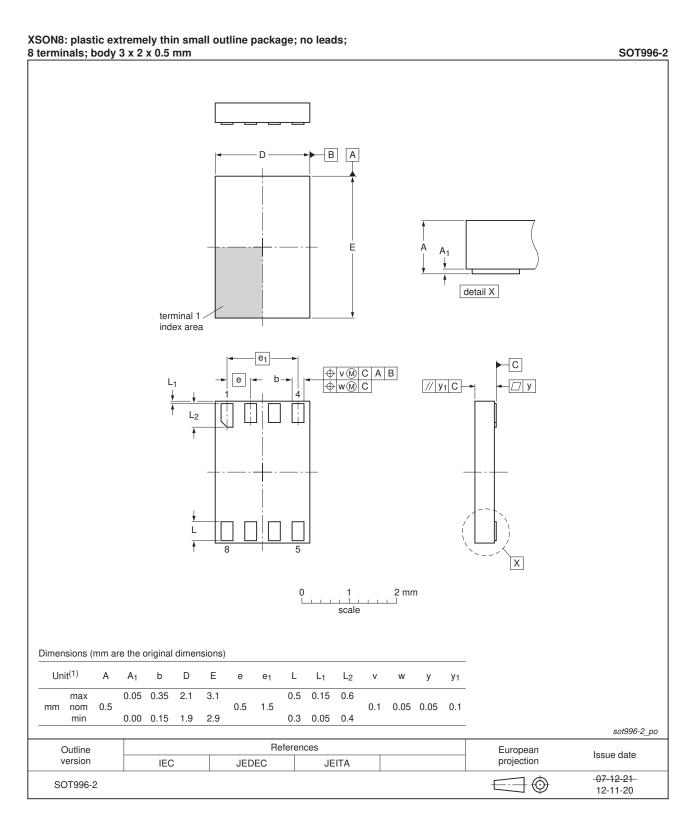


Fig 13. Package outline SOT996-2 (XSON8)

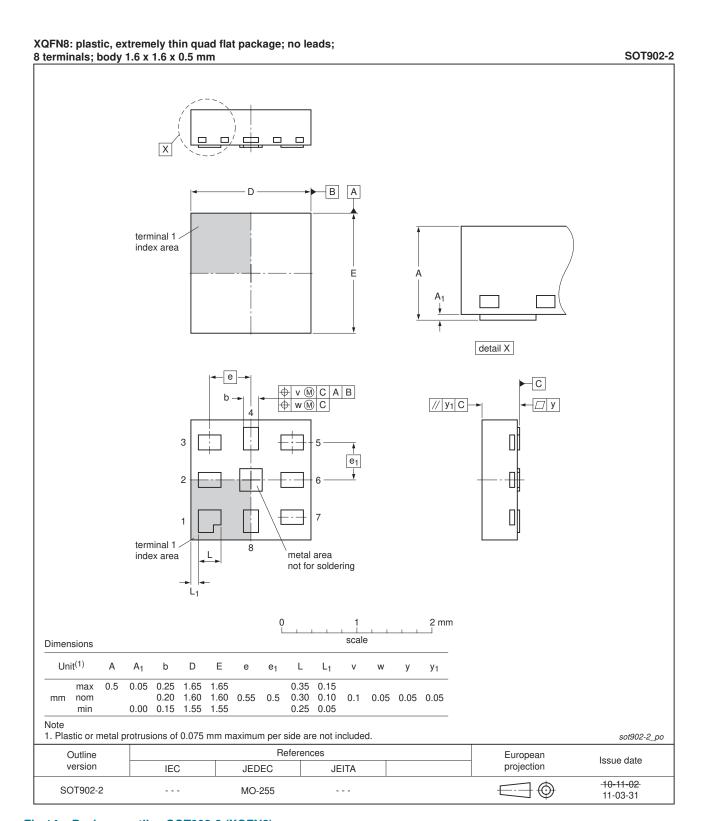


Fig 14. Package outline SOT902-2 (XQFN8)

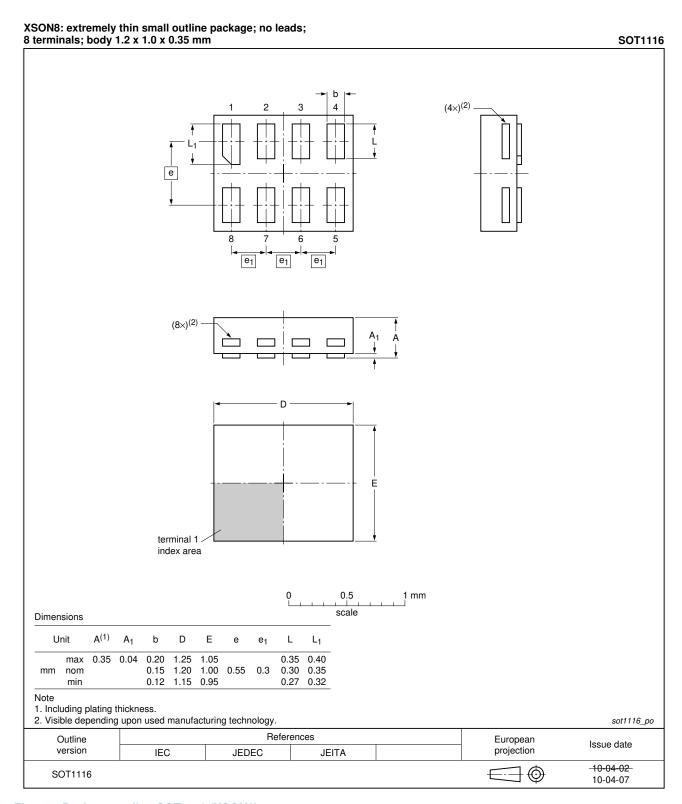


Fig 15. Package outline SOT1116 (XSON8)

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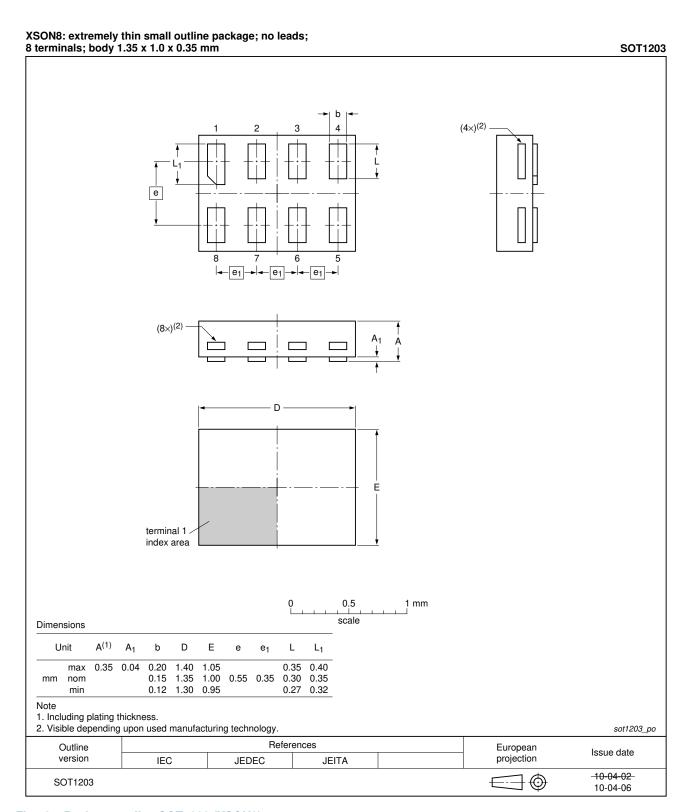


Fig 16. Package outline SOT1203 (XSON8)

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14. Abbreviations

Table 12. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP2G126 v.9	20130211	Product data sheet	-	74AUP2G126 v.8
Modifications:	 For type nun 	mber 74AUP2G126GD XSON8	BU has changed to XS	ON8.
74AUP2G126 v.8	20120606	Product data sheet	-	74AUP2G126 v.7
74AUP2G126 v.7	20111201	Product data sheet	-	74AUP2G126 v.6
74AUP2G126 v.6	20100621	Product data sheet	-	74AUP2G126 v.5
74AUP2G126 v.5	20090202	Product data sheet	-	74AUP2G126 v.4
74AUP2G126 v.4	20090114	Product data sheet	-	74AUP2G126 v.3
74AUP2G126 v.3	20080409	Product data sheet	-	74AUP2G126 v.2
74AUP2G126 v.2	20070515	Product data sheet	-	74AUP2G126 v.1
74AUP2G126 v.1	20061009	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Low-power dual buffer/line driver; 3-state

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17. Contact information

For more information, please visit: http://www.nxp.com

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Low-power dual buffer/line driver; 3-state

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